

# Emitter common (dual digital transistors)

## EMG3 / UMG3N / FMG3A

●Features

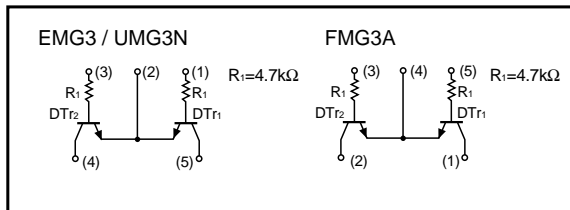
- 1) Two DTC143T chips in a EMT or UMT or SMT package.
- 2) Mounting cost and area can be cut in half.

●Structure

Dual NPN digital transistor  
(each with a single built in resistors)

The following characteristics apply to both the DT<sub>r1</sub> and DT<sub>r2</sub>.

●Equivalent circuit

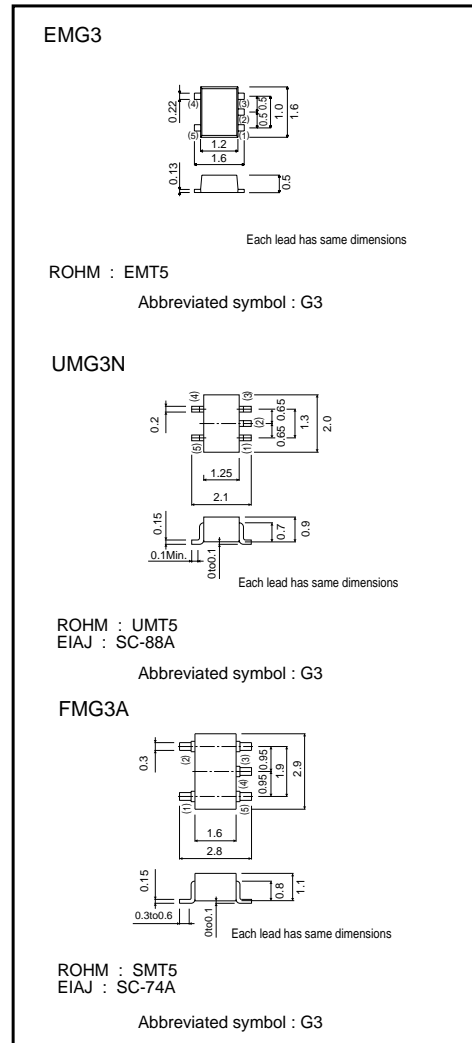


●Absolute maximum ratings (T<sub>a</sub> = 25°C)

| Parameter                   | Symbol           | Limits      | Unit  |
|-----------------------------|------------------|-------------|-------|
| Collector-base voltage      | V <sub>CB0</sub> | 50          | V     |
| Collector-emitter voltage   | V <sub>CE0</sub> | 50          | V     |
| Emitter-base voltage        | V <sub>EB0</sub> | 5           | V     |
| Collector current           | I <sub>c</sub>   | 100         | mA    |
| Collector power dissipation | EMG3, UMG3N      | 150 (TOTAL) | mW *1 |
|                             | FMG3A            | 300 (TOTAL) | mW *2 |
| Junction temperature        | T <sub>j</sub>   | 150         | °C    |
| Storage temperature         | T <sub>stg</sub> | -55 to +150 | °C    |

\*1 120mW per element must not be exceeded.  
\*2 200mW per element must not be exceeded.

●External dimensions (Unit : mm)



Transistors

●Electrical characteristics (Ta = 25°C)

| Parameter                            | Symbol               | Min. | Typ. | Max. | Unit | Conditions  |
|--------------------------------------|----------------------|------|------|------|------|---|
| Collector-base breakdown voltage     | BV <sub>CB0</sub>    | 50   | –    | –    | V    | I <sub>c</sub> =50μA                                    |
| Collector-emitter breakdown voltage  | BV <sub>CE0</sub>    | 50   | –    | –    | V    | I <sub>c</sub> =1mA                                     |
| Emitter-base breakdown voltage       | BV <sub>EB0</sub>    | 5    | –    | –    | V    | I <sub>E</sub> =50μA                                    |
| Collector cutoff current             | I <sub>CB0</sub>     | –    | –    | 0.5  | μA   | V <sub>CB</sub> =50V                                    |
| Emitter cutoff current               | I <sub>EB0</sub>     | –    | –    | 0.5  | μA   | V <sub>EB</sub> =4V                                     |
| Collector-emitter saturation voltage | V <sub>CE(sat)</sub> | –    | –    | 0.3  | V    | I <sub>c</sub> /I <sub>B</sub> =5mA/0.25mA              |
| DC current transfer ratio            | h <sub>FE</sub>      | 100  | 250  | 600  | –    | V <sub>CE</sub> =5V, I <sub>c</sub> =1mA                |
| Transition frequency                 | f <sub>T</sub>       | –    | 250  | –    | MHz  | V <sub>CE</sub> =10V, I <sub>E</sub> = –5mA, f=100MHz * |
| Input resistance                     | R <sub>1</sub>       | 3.29 | 4.7  | 6.11 | kΩ   | –   |

\* Transition frequency of the transistor

●Packaging specifications

| Type  | Package                      | Taping |      |      |
|-------|------------------------------|--------|------|------|
|       | Code                         | T2R    | TR   | T148 |
|       | Basic ordering unit (pieces) | 8000   | 3000 | 3000 |
| EMG3  | ○                            | —      | —    | —    |
| UMG3N | —                            | ○      | —    | —    |
| FMG3A | —                            | —      | —    | ○    |

●Electrical characteristic curves

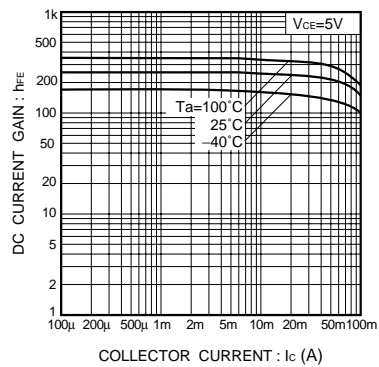


Fig.1 DC current gain vs. collector current

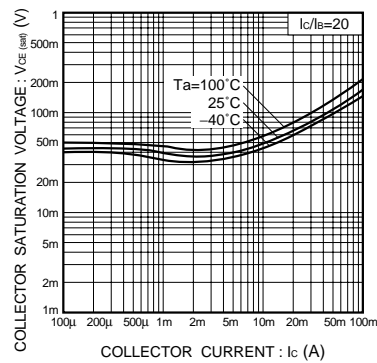


Fig.2 Collector-emitter saturation voltage vs. collector current

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